



SIHP25N60EFL-GE3 Information



For Reference Only

Part Number SIHP25N60EFL-GE3 **Manufacturer** Vishay Siliconix

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 600V 25A TO220AB

Package TO-220-3

For the pricing/inventory/lead time, please contact

us

Website: https://www.heisener.com E-mail: salesdept@heisener.com



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SIHP25N60EFL-GE3 Specifications

Manufacturer Part NumberSIHP25N60EFL-GE3ManufacturerVishay SiliconixCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-220-3SeriesEFET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C25A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250µAGate Charge (Qg) (Max) @ Vgs75nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2274pF @ 100VVgs (Max)±30VFET Feature-Power Dissipation (Max)250W (Tc)Rds On (Max) @ Id, Vgs146 mOhm @ 12.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3Report errors?		
Category Discrete Semiconductor Products Package TO-220-3 Series E FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 600V Current - Continuous Drain (Id) @ 25°C 25A (Tc) Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250µA Gate Charge (Qg) (Max) @ Vgs 75nC @ 10V Input Capacitance (Ciss) (Max) @ Vds 2274pF @ 100V Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 250W (Tc) Rds On (Max) @ Id, Vgs 146 mOhm @ 12.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Manufacturer Part Number	SIHP25N60EFL-GE3
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SeriesEFET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C25A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs75nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2274pF @ 100VVgs (Max)±30VFET Feature-Power Dissipation (Max)250W (Tc)Rds On (Max) @ Id, Vgs146 mOhm @ 12.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3		Transistors - FETs, MOSFETs - Single
FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C25A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs75nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2274pF @ 100VVgs (Max)±30VFET Feature-Power Dissipation (Max)250W (Tc)Rds On (Max) @ Id, Vgs146 mOhm @ 12.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Package	TO-220-3
TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C25A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs75nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2274pF @ 100VVgs (Max)±30VFET Feature-Power Dissipation (Max)250W (Tc)Rds On (Max) @ Id, Vgs146 mOhm @ 12.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	Series	E
Drain to Source Voltage (Vdss)600VCurrent - Continuous Drain (Id) @ 25°C25A (Tc)Drive Voltage (Max Rds On, Min Rds On)10VVgs(th) (Max) @ Id5V @ 250μAGate Charge (Qg) (Max) @ Vgs75nC @ 10VInput Capacitance (Ciss) (Max) @ Vds2274pF @ 100VVgs (Max)±30VFET Feature-Power Dissipation (Max)250W (Tc)Rds On (Max) @ Id, Vgs146 mOhm @ 12.5A, 10VOperating Temperature-55°C ~ 150°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3	FET Type	N-Channel
Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) 10V Vgs(th) (Max) @ Id 5V @ 250μA Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 146 mOhm @ 12.5A, 10V Operating Temperature Supplier Device Package Package / Case 25A (Tc) 25A (Tc) 25A (Tc) 25A (Tc) 16V 5V @ 250μA 5V @ 250μA 2274pF @ 100V 2274pF @ 100V 2274pF @ 100V 250W (Tc) Though Hole	Technology	MOSFET (Metal Oxide)
Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id St @ 250μA Gate Charge (Qg) (Max) @ Vgs T5nC @ 10V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 146 mOhm @ 12.5A, 10V Operating Temperature Supplier Device Package Package / Case TO-220AB TO-220-3	Drain to Source Voltage (Vdss)	600V
Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 146 mOhm @ 12.5A, 10V Operating Temperature Supplier Device Package Package / Case TO-220AB TO-220-3	Current - Continuous Drain (Id) @ 25°C	25A (Tc)
Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 2274pF @ 100V Vgs (Max) ±30V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 146 mOhm @ 12.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case TO-220AB TO-220-3	Drive Voltage (Max Rds On, Min Rds On)	10V
Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 146 mOhm @ 12.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Vgs(th) (Max) @ Id	5V @ 250μA
Vgs (Max) ±30V FET Feature - Power Dissipation (Max) 250W (Tc) Rds On (Max) @ Id, Vgs 146 mOhm @ 12.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Gate Charge (Qg) (Max) @ Vgs	75nC @ 10V
FET Feature - Power Dissipation (Max) 250W (Tc) Rds On (Max) @ Id, Vgs 146 mOhm @ 12.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Input Capacitance (Ciss) (Max) @ Vds	2274pF @ 100V
Power Dissipation (Max) Rds On (Max) @ Id, Vgs 146 mOhm @ 12.5A, 10V Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Vgs (Max)	±30V
Rds On (Max) @ Id, Vgs Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	FET Feature	-
Operating Temperature -55°C ~ 150°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Power Dissipation (Max)	250W (Tc)
Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3	Rds On (Max) @ Id, Vgs	146 mOhm @ 12.5A, 10V
Supplier Device Package TO-220AB Package / Case TO-220-3	Operating Temperature	-55°C ~ 150°C (TJ)
Package / Case TO-220-3	Mounting Type	Through Hole
	Supplier Device Package	TO-220AB
Report errors?	Package / Case	TO-220-3
		Report errors?

SIHP25N60EFL-GE3 Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

SIHP25N60EFL-GE3 Payment Methods



















SIHP25N60EFL-GE3 Shipping Methods













If you have any question about SIHP25N60EFL-GE3, please do not hesitate to contact us!

Website: https://www.heisener.com E-mail: salesdept@heisener.com